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Contents

KEYNOTE SESSION

11612 05 **Nano-scale effects of selective spin-on deposition** [11612-3]

RESIST CHEMISTRY: JOINT SESSIONS WITH CONFERENCES 11609 AND 11612

11612 07 **Improved non-CAR type hemicellulose resists for EUV lithography** [11612-5]

MOR AND INFILTRATION METHODS: JOINT SESSIONS WITH CONFERENCES 11609 AND 11612

11612 08 **Development of metal-organic cluster based negative tone resist: pre-screened through the helium-ion beam prelude to extreme ultraviolet lithography (EUVL) applications** [11612-7]

11612 09 **Preventing method of volume expansion of polymer after metal infiltration** [11612-8]

11612 0A **Hybrid resist synthesis by ex-situ vapor-phase infiltration of metal oxides into conventional organic resists** [11612-9]

RESIST FUNDAMENTALS

11612 0C **Probing ion diffusion in chemically amplified resists through experiments and atomistic simulations** [11612-11]

11612 0D **Fundamental study of polymer dynamic behavior in resist processing** [11612-12]

11612 0E **Chemistry working for lithography: the Marangoni-effect-based single layer for enhanced planarization** [11612-39]

UNDERLAYERS AND DEFECT REDUCTION

11612 0F **Reducing the absorbance of a high etch resistant spin-on carbon hardmask** [11612-15]

11612 0G **Development of metal purifiers specific to lithography materials** [11612-17]

11612 0H **High performance filtration for bulk materials: a novel HDPE membrane filter designed for EUV lithography** [11612-19]

NOVEL RESIST CONCEPTS AND TRACK PROCESSES

11612 0I **Multidimensional process optimization of a negative e-beam photoresist for silicon-waveguide manufacturing** [11612-20]

11612 0J **Highly fluorinated alternating copolymers possessing high glass transition temperature and cross-linking capabilities under extreme UV radiation** [11612-21]

11612 0L **EUV resist performance enhancement by UV flood exposure for high NA EUV lithography** [11612-23]

11612 0M **EUV lithographic process enablement with novel litho track hardware** [11612-24]

DSA

11612 0N **Self-aligned double pattern process using DSA pattern** [11612-25]

11612 0O **Top-coats for scalable nano-manufacturing with high-χ block copolymers in lithographic applications** [11612-26]

11612 0Q **Spatial arrangement of block copolymer nanopatterns using photoactive homopolymer substrates** [11612-29]

POSTER SESSION

11612 0R **Analysis of dissolution kinetics of poly(4-hydroxystyrene) with different molecular weight distributions in alkaline aqueous solution using machine learning** [11612-30]

11612 0S **Next generation purification method for achieving low trace metals in ultra-high purity chemicals** [11612-31]

11612 0T **EUV defect reduction activities using coater/developer and etching technique** [11612-32]

11612 0U **High contact angle embedded barrier layer materials for next-generation 193 immersion lithography** [11612-33]

11612 0V **Enabling EUV pattern transfer by optimized under layer** [11612-34]

11612 0W **Sequential infiltration synthesis and pattern transfer using 6 nm half-pitch carbohydrate-based fingerprint block copolymer** [11612-35]

11612 0X **Optimization of point-of-use filtration for metal oxide photoresist** [11612-36]

11612 10 **Modeling the acid-catalyzed cleavage of carbon-oxygen bonds** [11612-38]